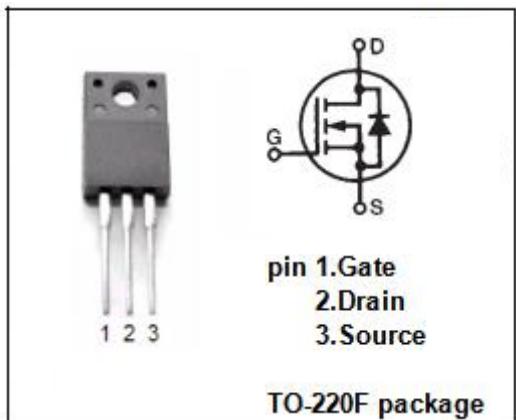


isc N-Channel MOSFET Transistor

TK7A80W

• FEATURES

- Low drain-source on-resistance:
 $R_{DS(on)} \leq 0.95\Omega$.
- Enhancement mode:
 $V_{th} = 3.0$ to 4.0 V ($V_{DS} = 10\text{ V}$, $I_D=0.28\text{mA}$)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

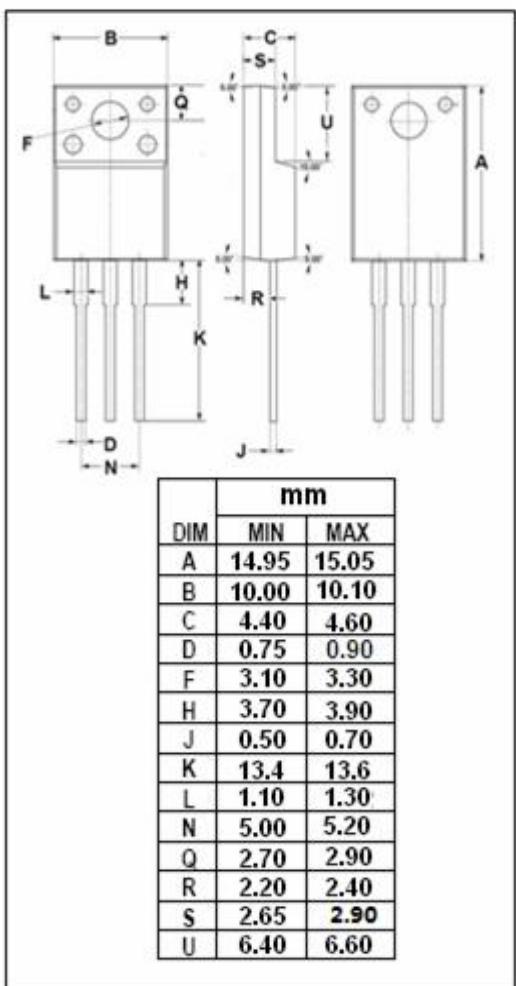


• DESCRIPTION

- Switching Voltage Regulators

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|--|----------|------------------|
| V_{DSS} | Drain-Source Voltage | 800 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| I_D | Drain Current-Continuous | 6.5 | A |
| I_{DM} | Drain Current-Single Pulsed | 26 | A |
| P_D | Total Dissipation @ $T_c=25^\circ\text{C}$ | 35 | W |
| T_j | Max. Operating Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | -55~150 | $^\circ\text{C}$ |



• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|----------------|------------------------------------|------|--------------------|
| $R_{th(ch-c)}$ | Channel-to-case thermal resistance | 3.57 | $^\circ\text{C/W}$ |

isc N-Channel MOSFET Transistor

TK7A80W

ELECTRICAL CHARACTERISTICS

 $T_c=25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------------------------------|--------------------------------|--|-----|-----|---------|------------------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $\text{V}_{\text{GS}}=0\text{V}; \text{I}_D=10\text{mA}$ | 800 | | | V |
| $\text{V}_{\text{GS}(\text{th})}$ | Gate Threshold Voltage | $\text{V}_{\text{DS}}=10\text{V}; \text{I}_D=0.28\text{mA}$ | 3.0 | | 4.0 | V |
| $\text{R}_{\text{DS}(\text{on})}$ | Drain-Source On-Resistance | $\text{V}_{\text{GS}}=10\text{V}; \text{I}_D=3.3\text{A}$ | | | 950 | $\text{m}\Omega$ |
| I_{GSS} | Gate-Source Leakage Current | $\text{V}_{\text{GS}}= \pm 20\text{V}; \text{V}_{\text{DS}}= 0\text{V}$ | | | ± 1 | μA |
| I_{DSS} | Drain-Source Leakage Current | $\text{V}_{\text{DS}}=800\text{V}; \text{V}_{\text{GS}}= 0\text{V}$ | | | 10 | μA |
| V_{SDF} | Diode forward voltage | $\text{I}_{\text{DR}} = 6.5\text{A}, \text{V}_{\text{GS}} = 0 \text{ V}$ | | | 1.7 | V |

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